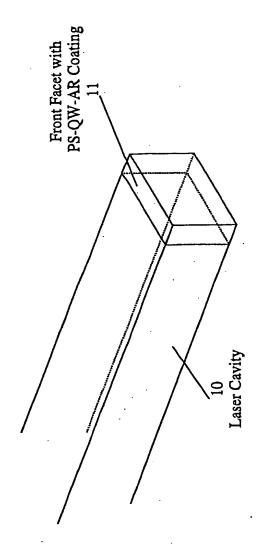
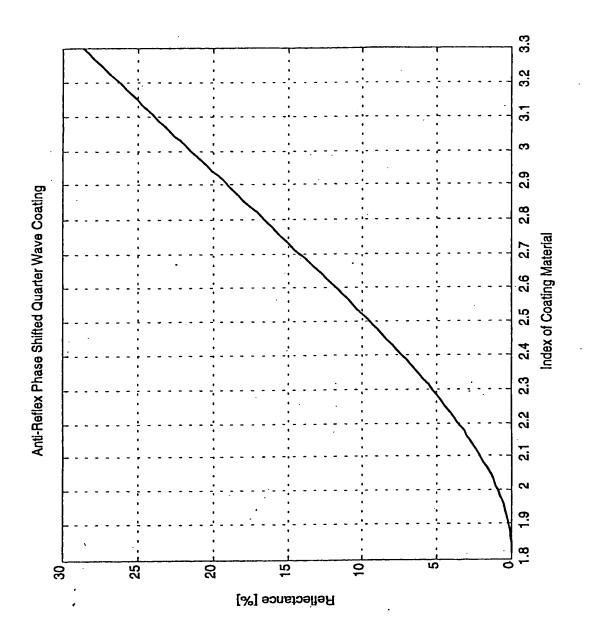


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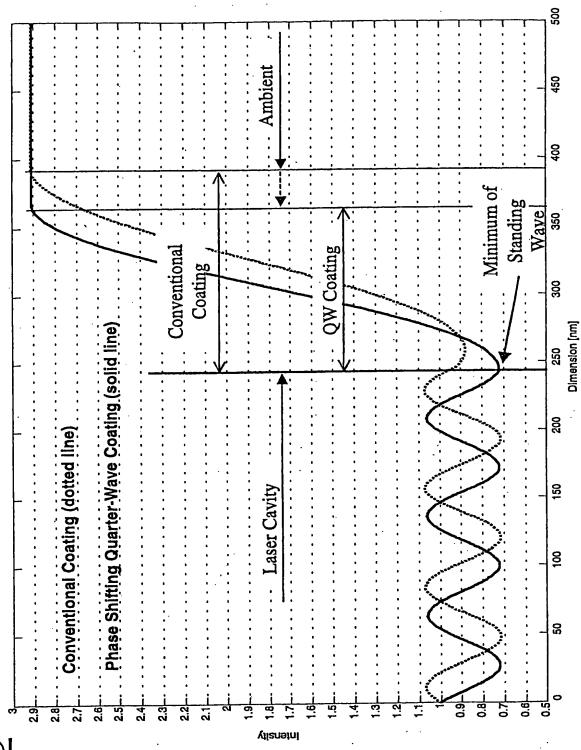


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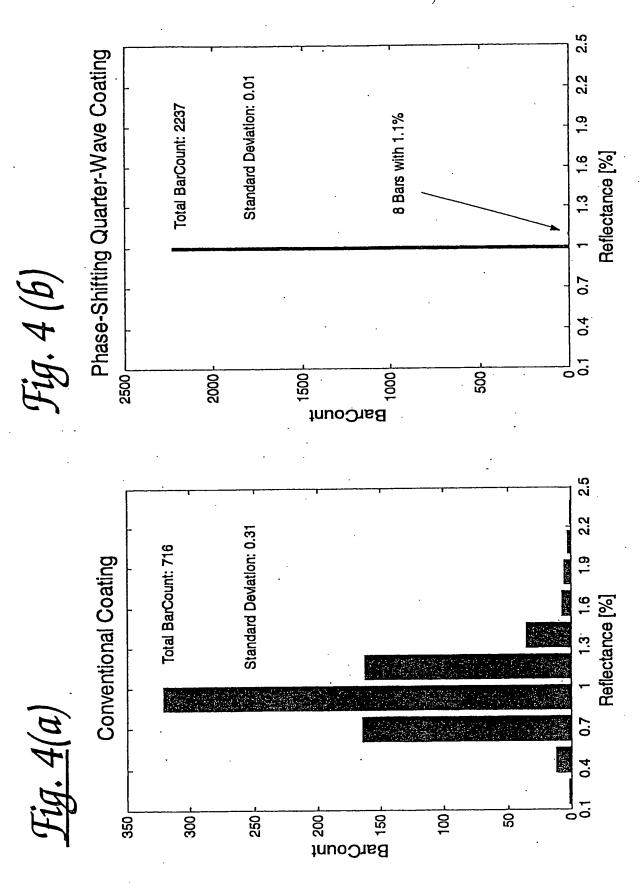


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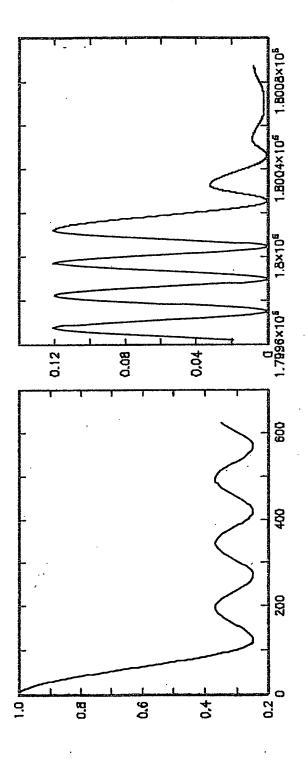




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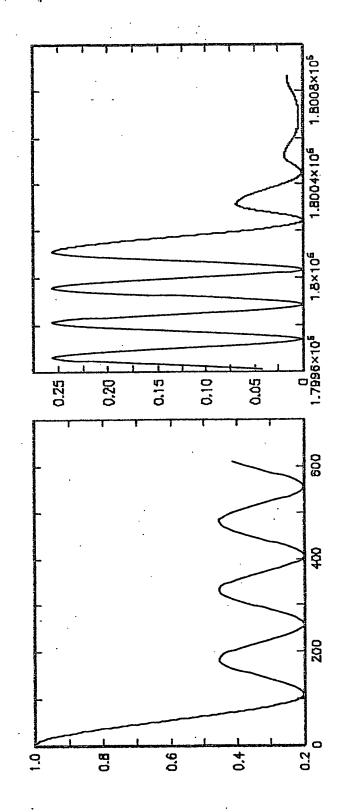


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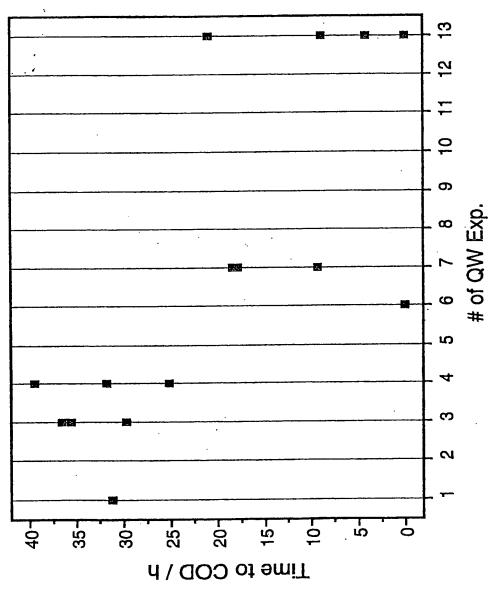
Phase Shifting Quarter Wave Coating with a 1 % Reflectance

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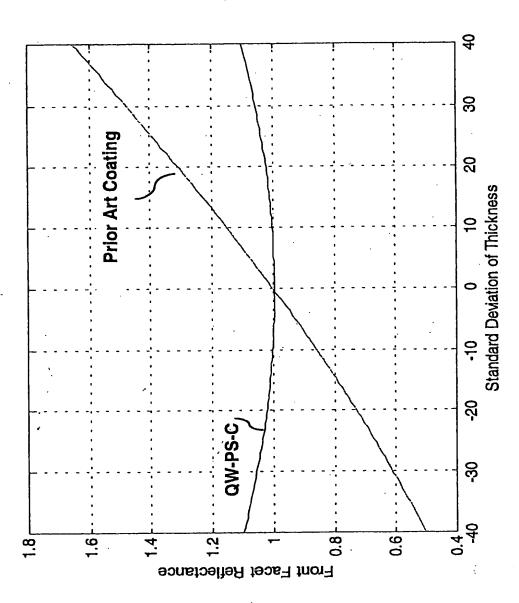
Phase Shifting Quarter Wave Coating with a 4 % Reflectance

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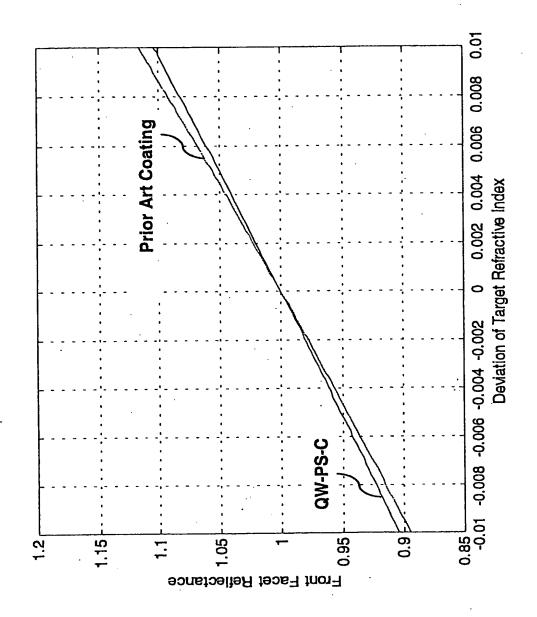
Time to COD vs. # of QW Exp

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Dependence of reflectance on thickness variation

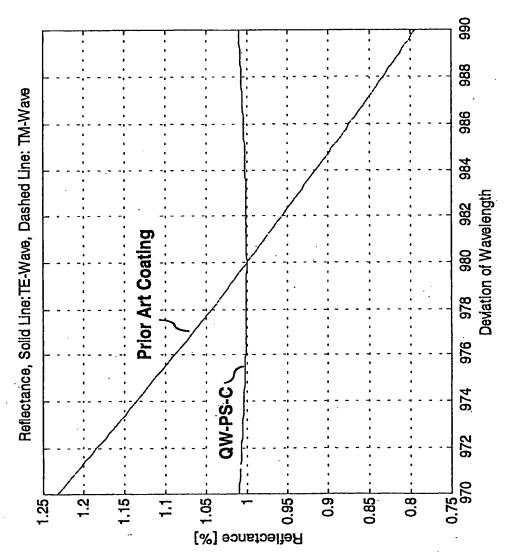
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Dependence of Reflectance on index variation



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Dependence of reflectance on wavelength variation

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Process parameters

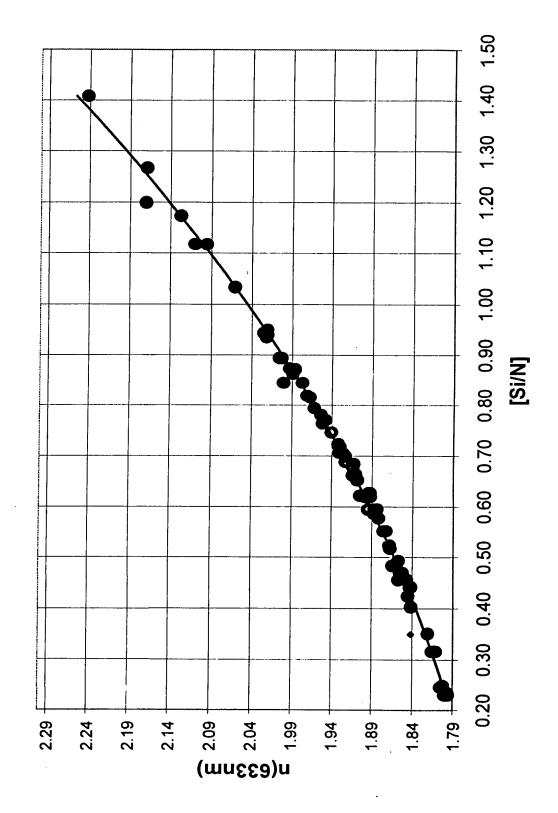
Reflectivity	index of refraction	Reflectivity index of refraction Substrate Temperature Pressure Plasma Power nitrogen flux	Pressure	Plasma Power	nitrogen flux		silane flux(*)
R	u	(S) S	r (10rr)	L plasma (W)	n _[N2] (SCCm)	n _{INH3J} (SCCIII)	II [SiH4] (SCCIII)
0.05%	1.86	300	1.4	25	35	18	236
1%	2.01	300	1.4	25	35	13	403
4%	2.23	300	1.4	25	35	8.5	491
1%(**)	1.83	300	1.4	20	330	11.2	300

(*) precursor gas of 2% SiH4 diluted in Helium (**) conventional non- $\lambda/4$ coating

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